"Incorporating ErAs into InGaAlBiAs Material by Interrupted Growth: Effects on Optical and Electronic Properties Targeting Terahertz Pulse Emitters and Detectors for Telecom Wavelength Excitation"

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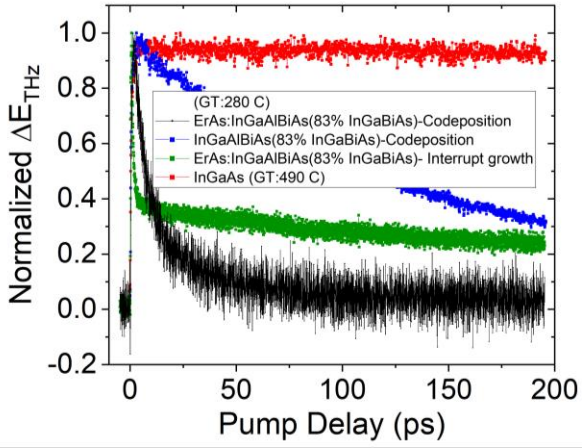
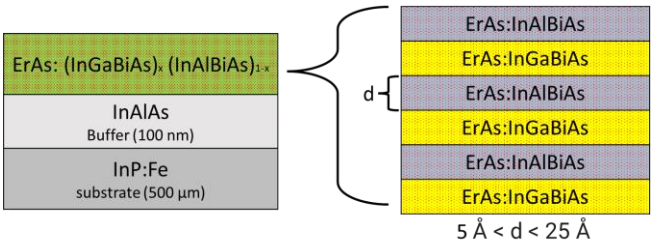
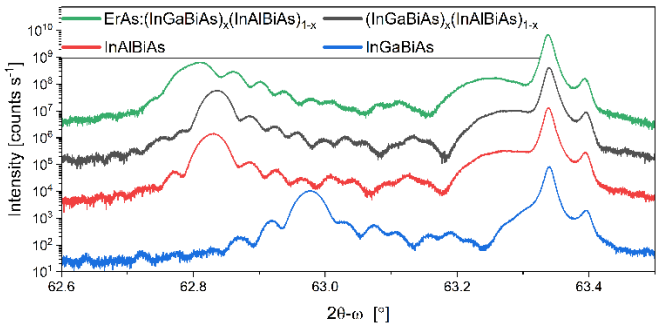
Supplemental figures:



1. Carrier dynamics measurement by Optical pump THz probe spectroscopy GT= Growth Temperature.



2. Structure representation of grown material.



3. High-resolution X-ray diffraction (004) 2θ − ω coupled scans of 300 nm strained [ErAs:(InGaBiAs)x (InAlBiAs)1−x] films with ~ 3.5% Bi and ~1% ErAs.